



**PRODUCT NAME :** 2SA1175 PNP General Purpose Transistor (Pack of 5)

**PRICE :** Rs 39.00

**SKU :** RM2133



NOTE: THE PRODUCT MAY BE DIFFERENT FROM IMAGE SHOWN. Copyrights by Robomart.com

## DESCRIPTION

## Features

- Collector-Emitter Volt ( $V_{ce0}$ ): 50V
- Collector-Base Volt ( $V_{cb0}$ ): 60V
- Collector Current ( $I_c$ ): 0.1A
- $h_{fe}$ : 110-600 @ 1mA
- Power Dissipation ( $P_{tot}$ ): 250mW
- Current-Gain-Bandwidth ( $f_{total}$ ): 180MHz
- Type: PNP

# NEC

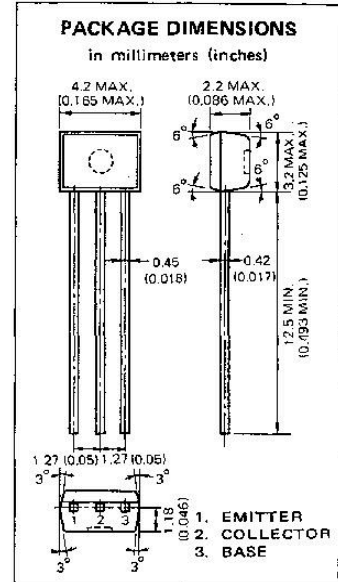
## PNP SILICON TRANSISTOR **2SA1175**

**DESCRIPTION** The 2SA1175 is designed for use in driver stage of AF amplifier.

- FEATURES**
- High  $h_{FE}$  and excellent linearity : 200 TYP.  
 $h_{FE}$  ( $I_C = -1.0$  mA)
  - Complementary to the NEC 2SC2785 NPN transistor.

**ABSOLUTE MAXIMUM RATINGS**

- Maximum Temperatures**
- Storage Temperature . . . . . -55 to +150 °C
  - Junction Temperature . . . . . +150 °C Maximum
- Maximum Power Dissipation ( $T_a = 25$  °C)**
- Total Power Dissipation . . . . . 250 mW
- Maximum Voltages and Currents ( $T_a = 25$  °C)**
- $V_{CBO}$  Collector to Base Voltage . . . . . -60 V
  - $V_{CEO}$  Collector to Emitter Voltage . . . . . -50 V
  - $V_{EBO}$  Emitter to Base Voltage . . . . . -5.0 V
  - $I_C$  Collector Current . . . . . -100 mA
  - $I_B$  Base Current . . . . . -20 mA



**ELECTRICAL CHARACTERISTICS ( $T_a = 25$  °C)**

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
$h_{FE}$	DC Current Gain	110	200	600	-	$V_{CE} = -6.0$ V, $I_C = -1.0$ mA
NF	Noise Figure		6.0	20	dB	$V_{CE} = -6.0$ V, $I_C = -0.3$ mA, $R_G = 10$ k $\Omega$ , $f = 100$ Hz
$f_T$	Gain Bandwidth Product	50	180		MHz	$V_{CE} = -6.0$ V, $I_E = -1.0$ mA
$C_{ob}$	Output Capacitance		4.5	6.0	pF	$V_{CB} = -10$ V, $I_E = 0$ , $f = 1.0$ MHz
$I_{CBO}$	Collector Cutoff Current			-0.1	$\mu$ A	$V_{CB} = -60$ V, $I_E = 0$
$I_{EBO}$	Emitter Cutoff Current			-0.1	$\mu$ A	$V_{EB} = -5.0$ V, $I_C = 0$
$V_{BE}$	Base to Emitter Voltage	-0.58	-0.62	-0.68	V	$V_{CE} = -6.0$ V, $I_C = -1.0$ mA
$V_{CE(sat)}$	Collector Saturation Voltage		-0.18	-0.3	V	$I_C = -100$ mA, $I_B = -10$ mA

**Classification of  $h_{FE}$**

Rank	RF	JF	HF	FF	EF	KF
Range	110 - 180	135 - 220	170 - 270	200 - 320	250 - 400	300 - 600

$h_{FE}$  Test Conditions:  $V_{CE} = -6.0$  V,  $I_C = -1.0$  mA

